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16. (Amended) A semiconductor device comprising a capacitor including a first electrode, a ferroelectric film formed above the first electrode, and a second electrode formed above the ferroelectric film, and a transistor connected to the first electrode or the second electrode and the ferroelectric film, and boundary between the ferroelectric film and the second electrode, materials of the intermediate layer being different from materials of the first electrode, the second electrode and the ferroelectric film.

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